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## (54) SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE

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#### (57)ABSTRACT

A semiconductor device includes a substrate; a first insulating layer provided on the substrate; a first metal layer provided on the first insulating layer; a second metal layer provided on the first metal layer; and a second insulating layer covering the first metal layer and the second metal layer. An upper surface of the first metal layer has a first region that is in contact with the second metal layer, and a second region that is separated from the second metal layer. The second insulating layer is in direct contact with a side surface and the second region of the first metal layer and an upper surface and a side surface of the second metal layer. A width of the first metal layer is greater than or equal to a width of the second metal layer in a direction parallel to the substrate.

